NSN 5962-01-372-6877

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1.5 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

7p blk 2 dcn, e/i fscm 49956

Features Provided:

Electrically alterable and programmable

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Case Outline Source And Designator:

D-9 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, memory, digital, cmos ee programmable array logic, monolithic silicon

Voltage Rating And Type Per Characteristic:

-0.5 volts total supply and 7.0 volts total supply

Time Rating Per Chacteristic:

15.00 nanoseconds access

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Specification Data:

67268-5962-89841 government standard

Specification Or Standard:

05 type and I case and a finish

Shelf Life:

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Demilitarization:

Yes - demil/mli

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